

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Hans-Joachim Müssig

Attorney Docket No.: 536-009.13 #2

Application No.: To be assigned

Group No.: To be assigned

Filed: Herewith

Examiner: To be assigned

For: SEMICONDUCTOR CAPACITOR AND MOSFET FITTED THEREWITH

Commissioner for Patents  
Director of the U.S. Patent & Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT

Sir:

Applicant submits herewith references of which they are aware, which they believe may be material to the examination of this application and in respect of which they may have a duty to disclose in accordance with 37 CFR 1.56.

While this Information Disclosure Statement may be "material" pursuant to 37 CFR 1.56, it is not intended to constitute an admission that any document referred to herein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined under 37 CFR 1.56(a) exists.

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

  
Sue Muro

Jan. 4, 2005  
Date

Attorney Docket No. 536-009.13  
Serial No. (to be assigned)

This IDS is being submitted simultaneously with the request for entry into the U.S. national phase corresponding to PCT application number PCT/EP03/07179 having international filing date of July 4, 2003. Therefore, the undersigned respectfully submits that no fee is due for filing this IDS. Should any fees be due of which the undersigned is unaware, the Commissioner is hereby authorized to charge deposit account 23-0442 any fee deficiency required to submit this IDS.

A PTO-1449 with cited references is enclosed.

Respectfully submitted,




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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO. 536-009.13		SERIAL NO. <b>10/520396</b> To be assigned			
				APPLICANT: Hans Joachim Müssig					
				FILING DATE: Herewith		ART UNIT: To be assigned			
<b>UNITED STATES PATENT DOCUMENTS</b>									
EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
	US	2002/0036313	3-28-2002	Sam Yang et al.					
	US	2003/0228747	12-11-2003	Kie Y. Ahn et al.					
	US	6,656,852	12-2-2003	Antonio Luis Pacheco Rotondaro et al.					
	US	2003/0119291	6-26-2003	Kie Y. Ahn					
	US	5,356,833	10-18-1994	Papu D. Maniar et al.					
	US	2003/0193061	10-16-2003	Hans-Jörg Osten					
<b>FOREIGN PATENT DOCUMENTS</b>									
		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO		
	WO	02/097895	12-5-2002	Dietmar Krüger et al.			abstract only		
<b>OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)</b>									
		Surface Science 504 (2002) 159-166, XP-001189099, <b>Initial stages of praseodymium oxide film formation on Si(001)</b> , H.-J. Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany; received 8 September 2001, accepted for publication 3 Dec. 2001.							
		2001 IRW Final Report, O-7803-7167-4/01/2001 IEEE, <b>Can Praseodymium Oxide be an Alternative High-K Gate Dielectric Material for Silicon Integrated Circuits?</b> , H.-J Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany.							
Examiner				Date:					